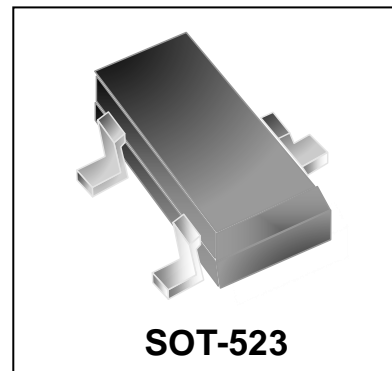


## N-Channel MOSFET

### Features

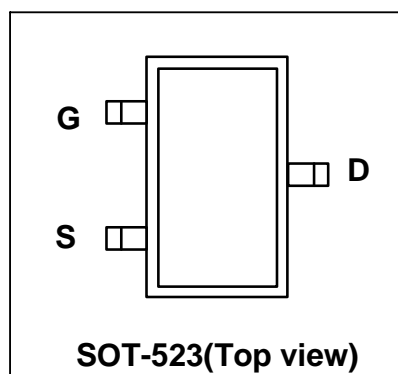
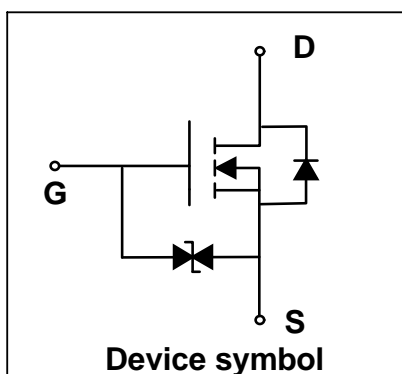
- $V_{DS} = 60V$ ,  $I_D = 0.34A$   
 $R_{DS(on)} < 2.1\Omega @ V_{GS} = 10V$   
 $R_{DS(on)} < 2.8\Omega @ V_{GS} = 4.5V$
- Voltage Controlled Small Signal Switch
- Rugged and Reliable
- High Saturation Current Capability
- ESD Protected



### Mechanical Characteristics

- SOT-523 Package
- Marking : Making Code
- RoHS Compliant

### Schematic & PIN Configuration



### Absolute Maximum Rating

Parameter	Symbol	Value	Unit
Drain-Source Voltage	$V_{DS}$	60	V
Continuous Drain Current ( $T_C = 25^\circ C$ )	$I_D$	340	mA
Pulsed Drain Current <sup>2</sup>	$I_{DM}$	1	A
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Power Dissipation ( $T_C = 25^\circ C$ )	$P_D$	150	mW
Junction Temperature	$T_J$	150	$^\circ C$
Storage Temperature	$T_{STG}$	-55 to +150	$^\circ C$
Thermal Resistance from Junction to Ambient <sup>1</sup>	$R_{\theta JA}$	833	$^\circ C/W$

**Electrical Characteristics** ( $T_{amb}=25^{\circ}\text{C}$  unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
<b>Static Characteristics</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	60	-	-	V
Gate Threshold Voltage <sup>3</sup>	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	1	1.3	2	V
Drain Cut-off Current	$I_{DSS}$	$V_{DS} = 60V, V_{GS} = 0V$	-	-	1	$\mu A$
Gate Leakage Current	$I_{GSS}$	$V_{GS} = \pm 20V, V_{DS} = 0V$	-	-	$\pm 10$	$\mu A$
Drain-Source on-State Resistance <sup>3</sup>	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 0.5A$	-	1.3	2.1	$\Omega$
		$V_{GS} = 4.5V, I_D = 0.2A$	-	1.4	2.8	$\Omega$
<b>Dynamic Characteristics</b>						
Input Capacitance	$C_{iss}$	$V_{DS} = 10V, V_{GS} = 0V,$ $f = 1MHz$	-	25	-	pF
Output Capacitance	$C_{oss}$		-	5.6	-	
Reverse Transfer Capacitance	$C_{rss}$		-	2.2	-	
<b>Switching Characteristics</b>						
Total Gate Charge <sup>4</sup>	$Q_g$	$V_{GS} = 4.5V, I_D = 0.25A,$ $V_{DS} = 10V$	-	0.3	-	nC
Gate-Source Charge <sup>4</sup>	$Q_{gs}$		-	0.2	-	
Gate-Drain Charge <sup>4</sup>	$Q_{gd}$		-	0.08	-	
Turn-on Time <sup>4</sup>	$t_{d(on)}$	$V_{DD} = 30V, I_D = 200mA,$ $R_G = 25\Omega, V_{GEN} = 10V$	-	3.9	-	nS
Rise Time <sup>4</sup>	$t_r$		-	3.4	-	
Turn-off Time <sup>4</sup>	$t_{d(off)}$		-	15.7	-	
Fall Time <sup>4</sup>	$t_f$		-	9.9	-	
<b>Reverse Diode Characteristics</b>						
Diode Forward Voltage <sup>3</sup>	$V_{SD}$	$V_{GS} = 0V, I_F = 0.3A$	-	-	1.5	V

**Notes:**

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper.
3. Pulse Test : Pulse Width $\leq 300\mu s$ , Duty Cycle $\leq 2\%$ .
4. Guaranteed by design, not subject to production.

Typical Characteristics

Figure 1. Output Characteristics

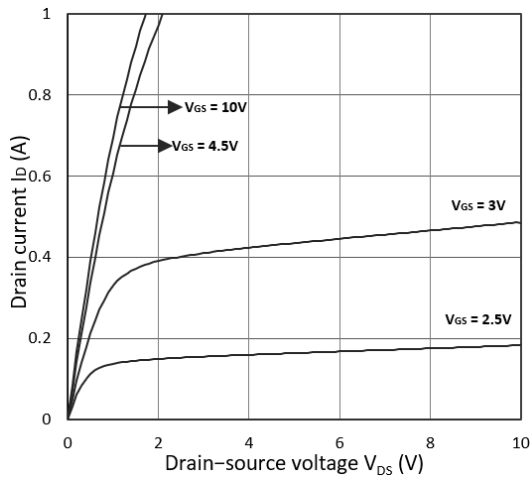


Figure 2. Transfer Characteristics

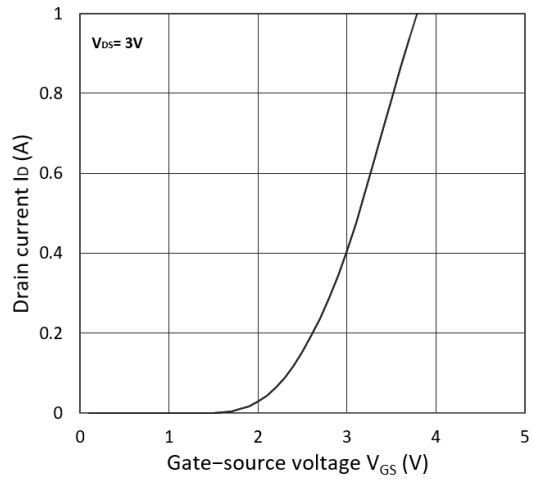


Figure 3.  $R_{DS(on)}$  vs.  $I_D$

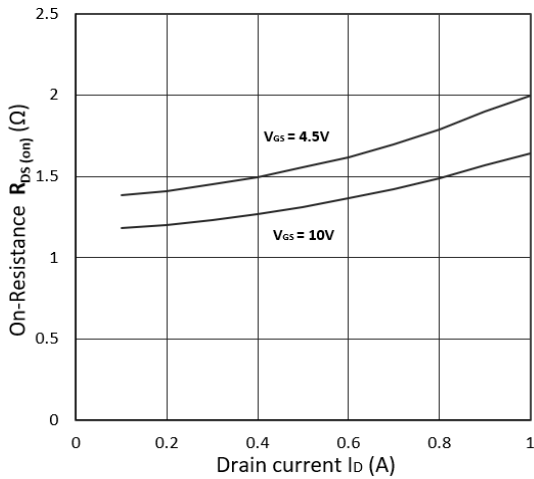


Figure 4.  $R_{DS(on)}$  vs.  $V_{GS}$

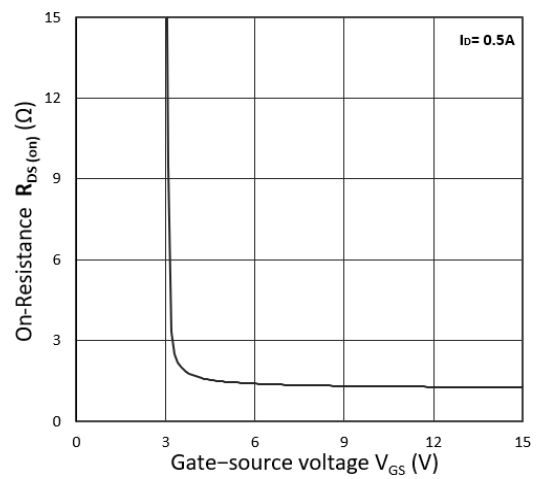


Figure 5.  $I_S$  vs.  $V_{SD}$

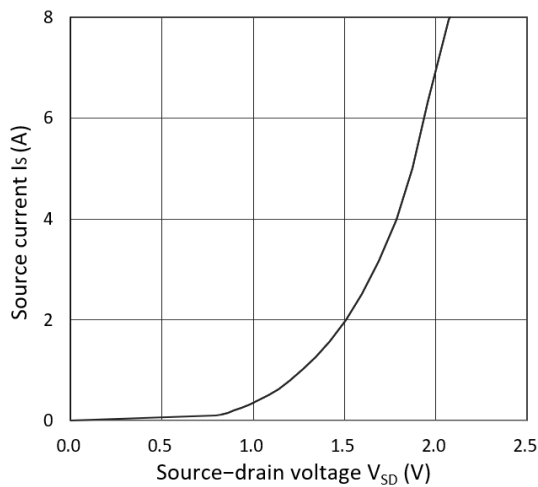
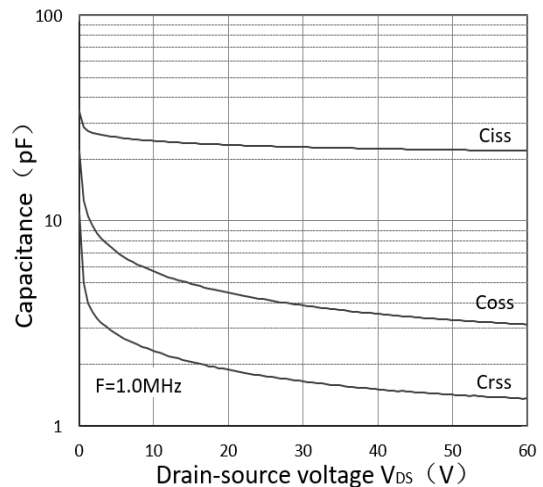


Figure 6. Capacitance Characteristics



Outline Drawing – SOT-523

### PACKAGE OUTLINE

**SOT-523**

SYM BOL	MILLIMETER		INCHES	
	MIN	MAX	MIN	MAX
A	0.7	0.9	0.028	0.035
A1	0	0.1	0	0.004
A2	0.7	0.8	0.028	0.031
b1	0.15	0.25	0.006	0.01
b2	0.25	0.35	0.01	0.014
c	0.1	0.2	0.004	0.008
D	1.5	1.7	0.059	0.067
E	0.7	0.9	0.028	0.035
E1	1.45	1.75	0.057	0.069
e1	0.9	1.1	0.035	0.043
L	0.3	0.5	0.012	0.02
L1	0.26	0.46	0.01	0.018
θ	0	8°	0	8°

DIMENSIONS		
DIM	INCHES	MILLIMETERS
C	.055	1.40
P	.039	1.00
P1	.020	0.50
G	.024	0.60
X	.016	0.40
Y	.031	0.80
Z	.087	2.20

**Notes**

1. Dimensioning and tolerances per ANSI Y14.5M, 1985.
2. Controlling Dimension: Inches
3. Pin 3 is the cathode (Unidirectional Only).
4. Dimensions are exclusive of mold flash and metal burrs.

**Marking Codes**

Part Number	WM06N03L
Marking Code	

**Package Information**

Qty: 3k/Reel

**CONTACT INFORMATION**

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WAYON website: <http://www.way-on.com>

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